KTC3199

Rev.E Mar.-2016

蓝箭电子 BLUE ROCKET ELECTRONICS

DATA SHEET

/ Descriptions

TO-92 NPN Silicon NPN transistor in a TO-92 Plastic Package.

/ Features

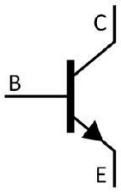
, h_{FE} , , KTA1267

High DC current gain, excellent h_{FE} linearity, low noise, complementary to KTA1267.

/ Applications

General amplifier and switching application.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Collector PIN 3 Emitter

/ hFE Classifications & Marking

h_{FE} Classifications Symbol	O	Y	GR	BL
h_{FE} Range	70~140	120~240	200~400	350~700

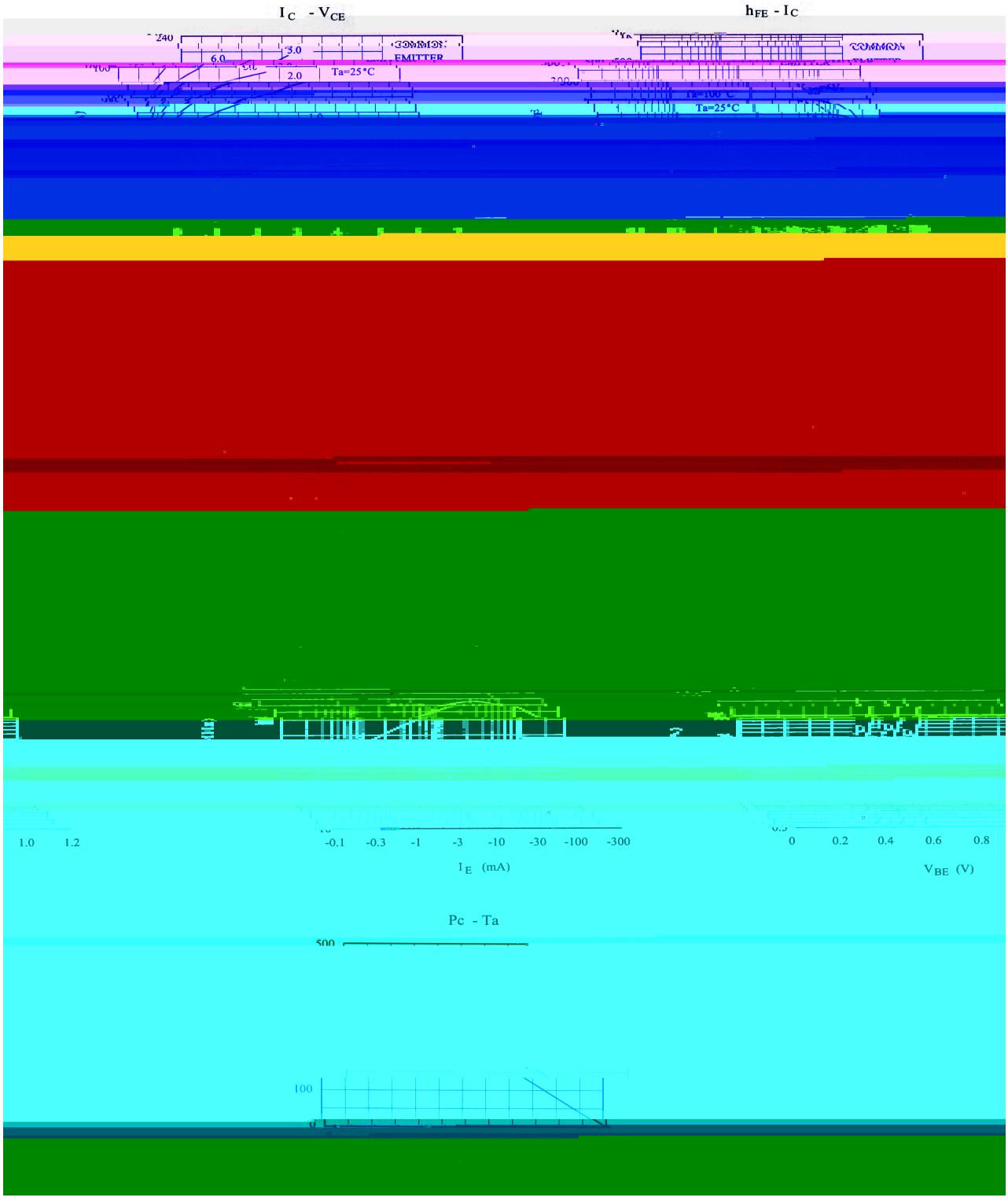
/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	50	V
Collector to Emitter Voltage	V_{CEO}	50	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	150	mA
Emitter Current - Continuous	I_E	-150	mA
Collector Power Dissipation	P_C	400	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

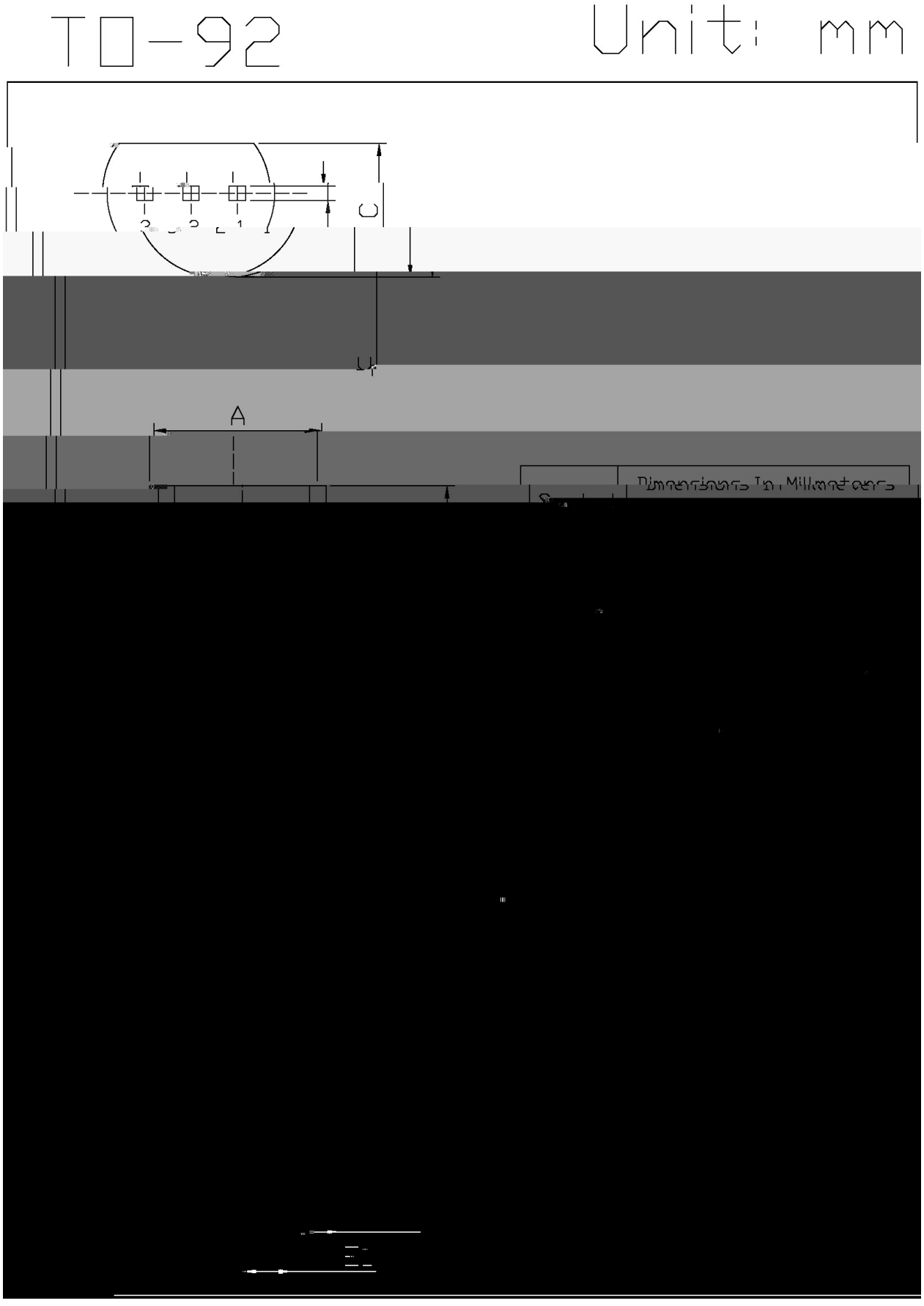
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	V_{CB}=50V I_E=0			0.1	A
Emitter Cut-Off Current	I_{EBO}	V_{EB}=5.0V I_C=0			0.1	A
DC Current Gain	h_{FE}	V_{CE}=6.0V I_C=2.0mA	70		700	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=100mA I_B=10mA		0.1	0.25	V
Transition Frequency	f_T	V_{CE}=10V I_C=1.0mA	80			MHz
Collector Capacitance	C_{ob}	V_{CB}=10V I_E=0 f=1.0MHz		2.0	3.5	pF
Noise Figure	NF	$_{CE}$=6.0V f=1.0KHz I_C=0.1mA R_g=10K		1.0	10	dB

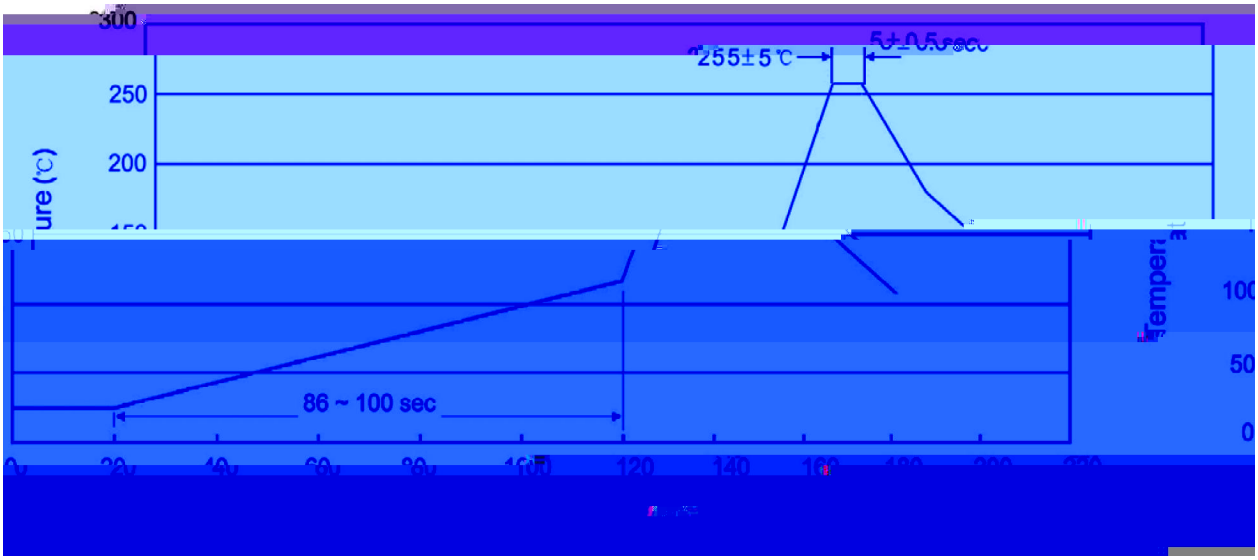
/ Electrical Characteristic Curve



/ Package Dimensions



( ) / Temperature Profile for Dip Soldering(Pb-Free)



					Note:
1		25	150	60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2		255±5		5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.
3			2 10	/sec.	3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270±5	10±1 sec.	Temp:270±5	Time:10±1 sec

/ Packaging SPEC.

/ BULK